

Si PNP TRANSISTOR—B834

DESCRIPTION AND FEATURES

*Collector-Emitter voltage: $BV_{CBO} = -60V$ *Collector current up to $-3A$ *High h_{FE} linearity

PIN CONFIGURATIONS

PIN	SYMBOL
1	Emitter
2	Collector
3	Base

ABSOLUTE MAXIMUM RATINGS (Tamb=25)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	BV_{CBO}	-60	V
Collector-Emitter Voltage	BV_{CEO}	-50	V
Emitter-Base Voltage	BV_{EBO}	-7	V
Collector Dissipation	Tcase=25	30	W
	Tamb=25	1.5	W
Collector Current	DC	I_{CM}	-3
	Pulse	I_{cp}	-7
Base Current	I_B	-0.6	A
Junction Temperature	T_j	+150	
Storage Temperature	T_{stg}	-55 ~ +150	

ELECTRICAL CHARACTERISTICS (Tamb=25 ,all voltage referenced to GND Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-100	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	nA
DC Current Gain	h_{FE1}	$V_{CE} = -5V, I_C = 20mA$	30	200		
	h_{FE2}	$V_{CE} = -5V, I_C = -0.5A$	100		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -3A, I_B = -0.3A$		-0.3	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -3A, I_B = -0.3A$		-1.0	-2.0	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -5V, I_C = -0.1A$		5		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		80		pF

CLASSIFICATION OF h_{FE}

RANK	Q	P	E
RANGE	100 ~ 200	160 ~ 320	200 ~ 400

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